

REMARKS

The claims have been amended to correct improper multiple dependencies, and to put the application into better form for examination.

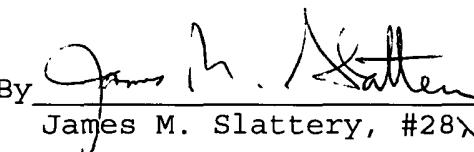
Entry of the above amendments is earnestly solicited. An early and favorable first action on the merits is earnestly solicited.

Attached hereto is a marked-up version of the changes made to the application by this Amendment.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. § 1.16 or under 37 C.F.R. § 1.17; particularly, extension of time fees.

Respectfully submitted,

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Attachment(s): VERSION WITH MARKINGS TO SHOW CHANGES MADE

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

The claims have been amended as follows:

4. (Amended) A method according to [any one of claims 1 to 3] claim 1, wherein the vertical planes are selected from one or more of the m-planes (1100) and the a-planes (1120).
6. (Amended) A method according to [any one of claims 2 to 5] claim 2, wherein the thickness of the substrate is less than about 400 μm .
8. (Amended) A method according to claim 6 [or claim 7], wherein the grooves are cut to a depth of from about 40 μm to about 100 μm .
10. (Amended) A method according to claim 8 [or claim 9], wherein the depth of said grooves is controlled by process parameters including the intensity of the laser beam, the speed at which the laser beam is scanned over the grooves and the number of times the laser beam is scanned over said grooves.
12. (Amended) A method according to claim 10 [or claim 11], wherein the average power of the laser beam is about 1.4W.

13. (Amended) A method according to [any one of claims 10 to 12] claim 10, wherein the repetition rate of the laser beam is from about 2 kHz to about 5 kHz.

14. (Amended) A method according to [any one of claims 10 to 13] claim 10, wherein the pulse width of the laser beam is from about 5 ns to about 30 ns.

15. (Amended) A method according to [any of claims 10 to 14] claim 10, wherein the laser beam is scanned over the second surface of the substrate from 2 to about 12 times at a velocity of about 1 mm/sec.

16. (Amended) A method according to [any one of claims 1 to 15] claim 1, wherein the at least one GaN-based layer includes a plurality of GaN-based layers.

17. (Amended) A method according to claim 16 [or claim 17], wherein the GaN-based layers are formed using epitaxial lateral overgrowth (ELOG) techniques.

18. (Amended) A laser device having cleaved facets formed according to the method of [any one of claims 1 to 18] claim 1.